

## QIAOXIN N-Channel **Super Trench** Power MOSFET

### Description

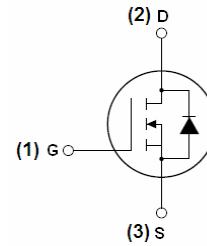
The VCRRP0160F uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### General Features

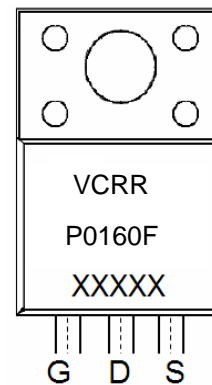
- $V_{DS} = 100V, I_D = 60A$   
 $R_{DS(ON)} = 9.2m\Omega$  (typical) @  $V_{GS} = 10V$
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

### Application

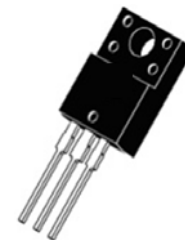
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Schematic diagram



Marking and pin assignment



TO-220F top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package
VCRRP0160F		TO-220F

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	60	A
Drain Current-Continuous ( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	42.4	A
Pulsed Drain Current	$I_{DM}$	240	A
Maximum Power Dissipation	$P_D$	35	W
Derating factor		0.23	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	290	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

## Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	4.3	$^{\circ}C/W$
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## Electrical Characteristics ( $T_C=25^{\circ}C$ unless otherwise noted)

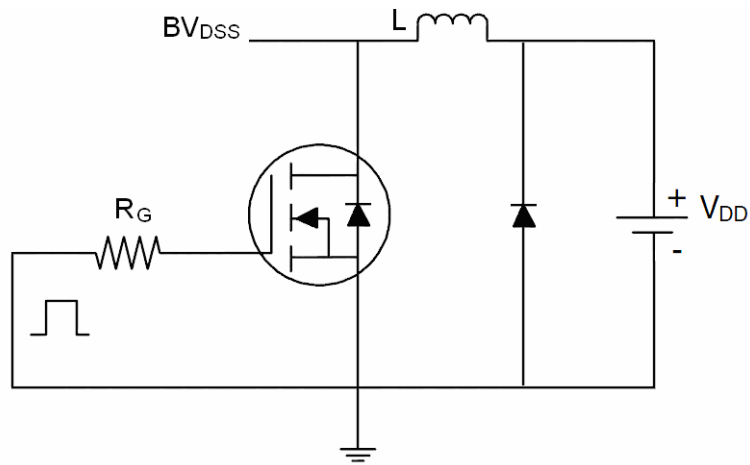
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	100		-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=100V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics</b> <sup>(Note 3)</sup>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=30A$	-	9.2	10.8	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=30A$	-	40	-	S
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>						
Input Capacitance	$C_{iss}$	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0MHz$	-	2500	-	PF
Output Capacitance	$C_{oss}$		-	273	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	27	-	PF
<b>Switching Characteristics</b> <sup>(Note 4)</sup>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=50V, I_D=30A$ $V_{GS}=10V, R_G=4.7\Omega$	-	13	-	nS
Turn-on Rise Time	$t_r$		-	8.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	29	-	nS
Turn-Off Fall Time	$t_f$		-	4	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=50V, I_D=30A,$ $V_{GS}=10V$	-	37		nC
Gate-Source Charge	$Q_{gs}$		-	14		nC
Gate-Drain Charge	$Q_{gd}$		-	8		nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=60A$	-		1.2	V
Diode Forward Current <sup>(Note 2)</sup>	$I_S$		-	-	60	A
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}C, I_F = I_S$ $di/dt = 100A/\mu s$ <sup>(Note 3)</sup>	-	58		nS
Reverse Recovery Charge	$Q_{rr}$		-	149		nC

### Notes:

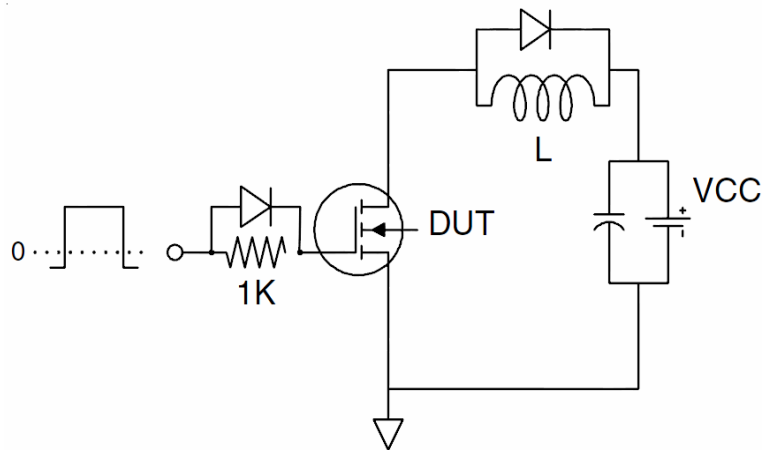
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition :  $T_J=25^{\circ}C, V_{DD}=50V, V_G=10V, L=0.5mH, R_G=25\Omega$

## Test Circuit

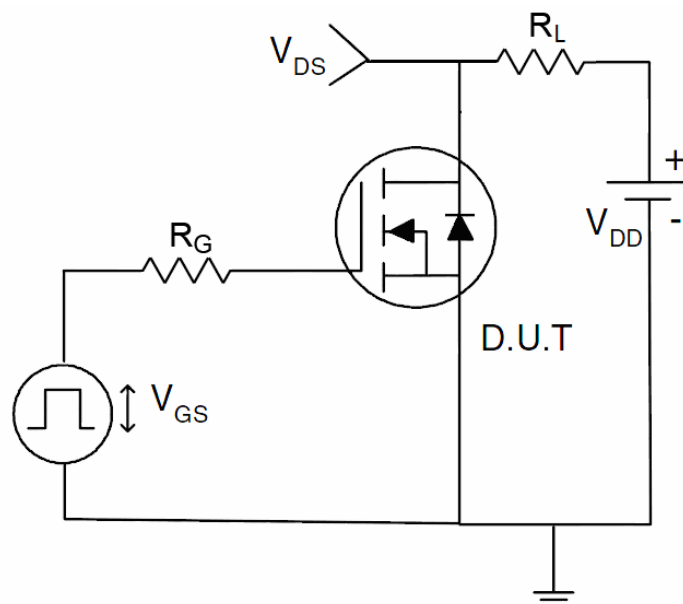
### 1) $E_{AS}$ test Circuit



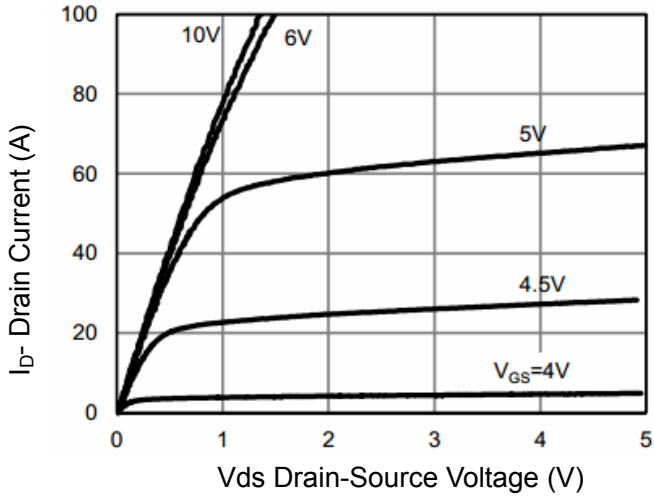
### 2) Gate charge test Circuit



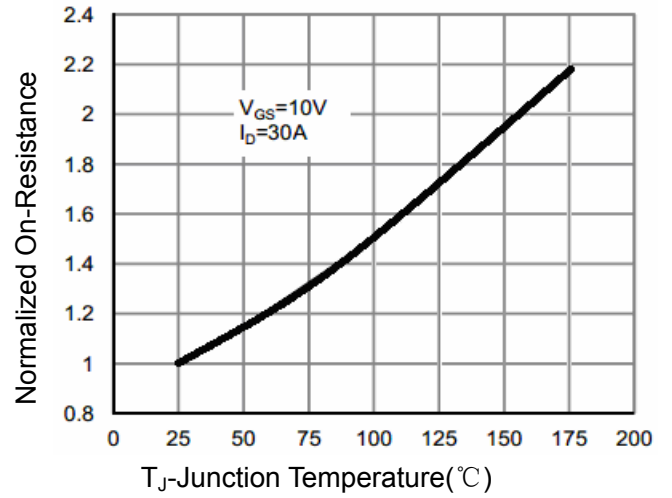
### 3) Switch Time Test Circuit



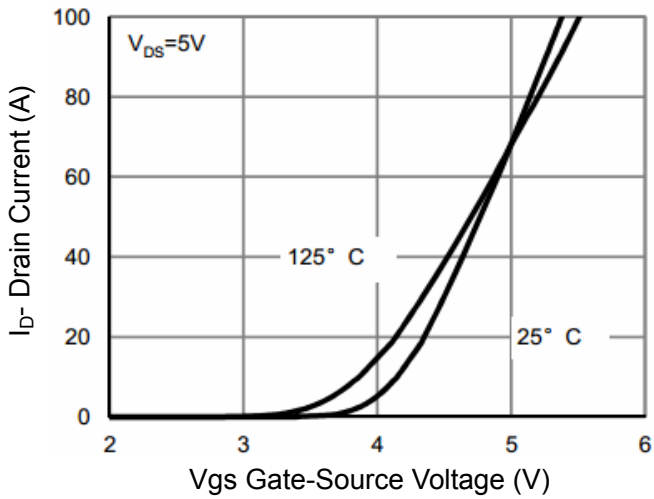
**Typical Electrical and Thermal Characteristics**



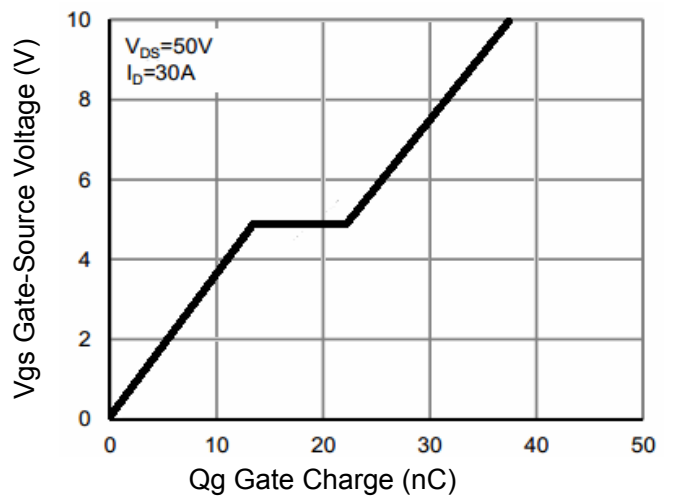
**Figure 1 Output Characteristics**



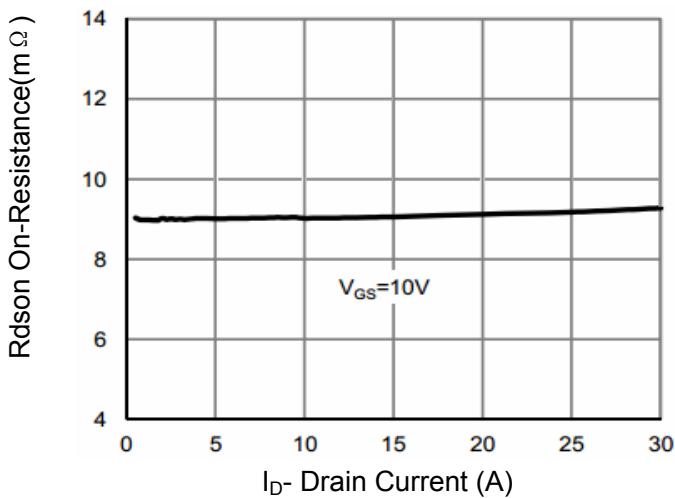
**Figure 4  $R_{dson}$ -Junction Temperature**



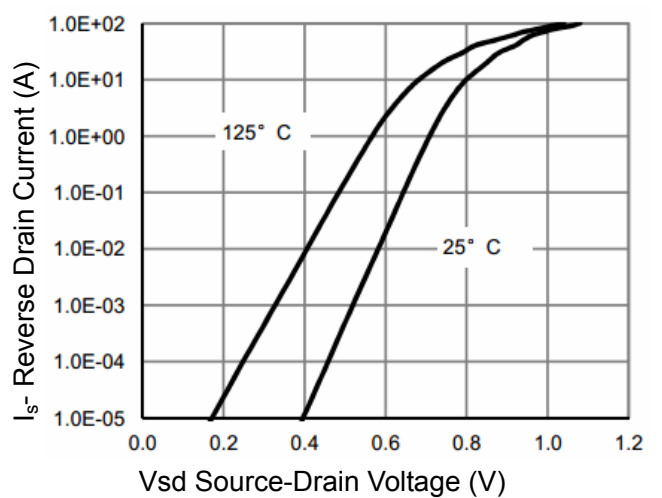
**Figure 2 Transfer Characteristics**



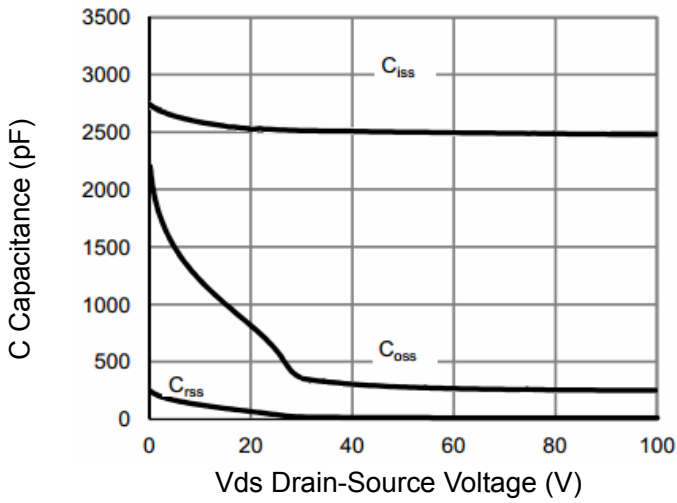
**Figure 5 Gate Charge**



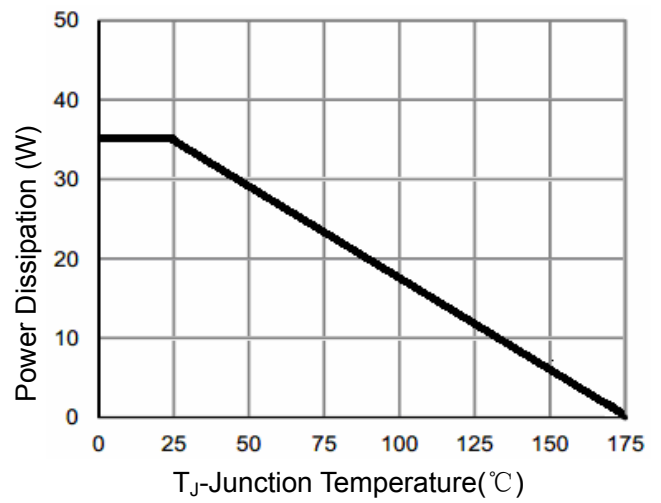
**Figure 3  $R_{dson}$ - Drain Current**



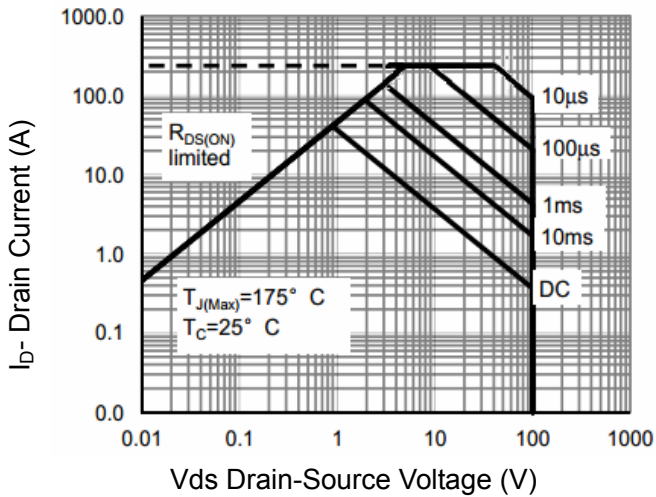
**Figure 6 Source- Drain Diode Forward**



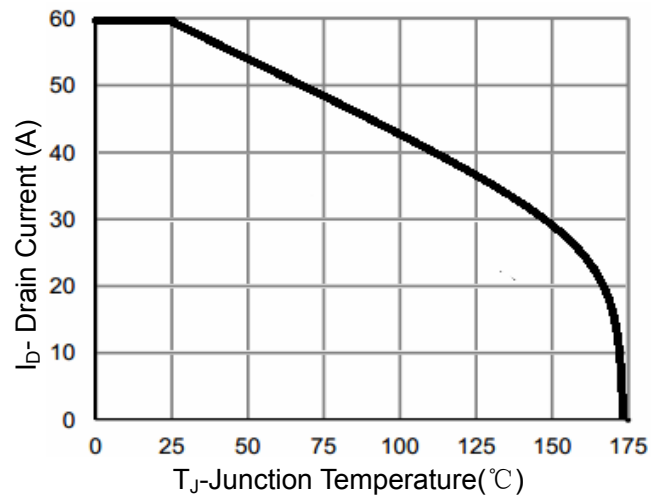
**Figure 7 Capacitance vs Vds**



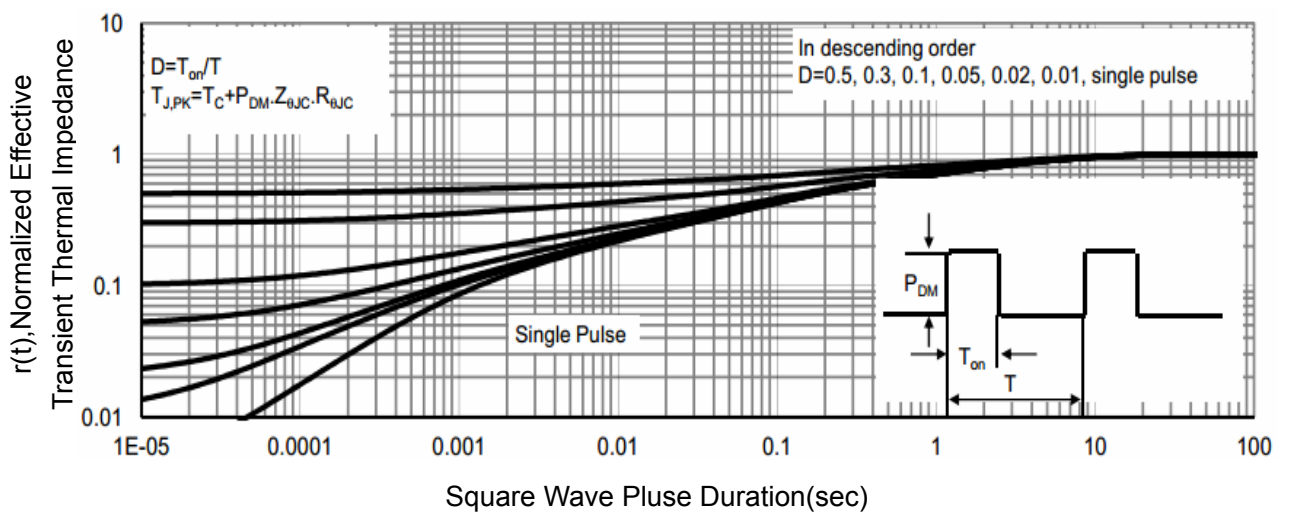
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area**

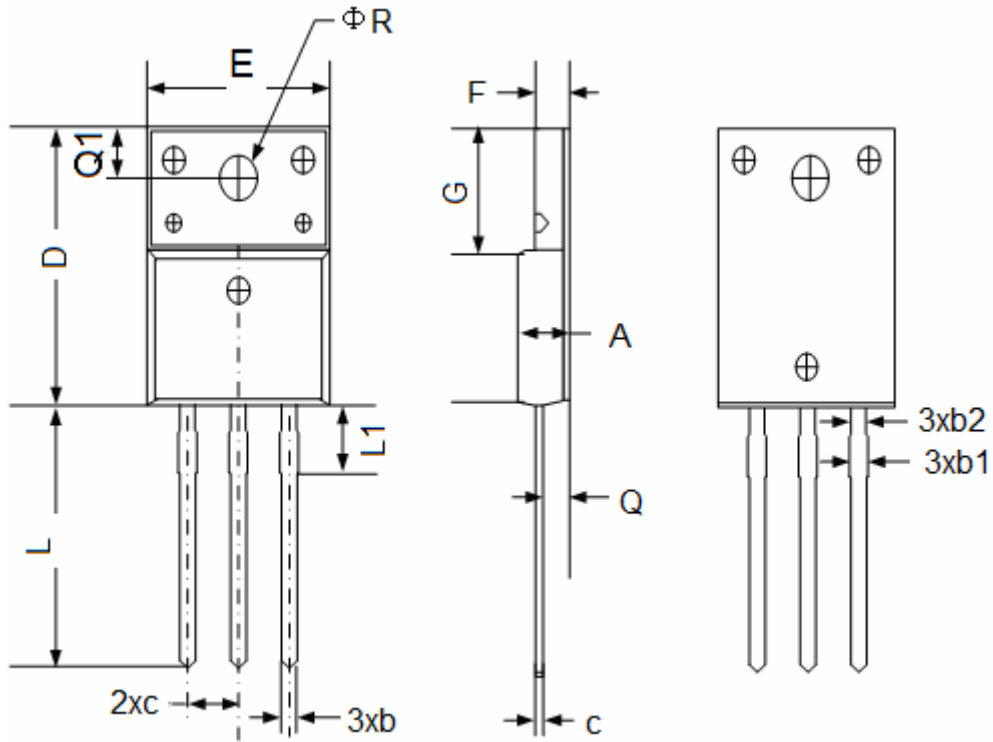


**Figure 10 Current De-rating**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

**TO-220F Package Information**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.50	4.83	0.18	0.19
b	0.70	0.91	0.03	0.04
b1	1.20	1.47	0.05	0.06
b2	1.10	1.38	0.04	0.05
c	0.45	0.63	0.02	0.02
D	15.67	16.07	0.62	0.63
e	2.54 BSC		0.10 BSC	
E	9.96	10.36	0.39	0.41
F	2.34	2.74	0.09	0.11
G	6.48	6.90	0.26	0.27
L	12.68	13.30	0.50	0.52
L1	3.13	3.50	0.12	0.14
Q	2.56	2.93	0.10	0.12
Q1	3.20	3.40	0.13	0.13
ΦR	3.08	3.28	0.12	0.13

### **Attention**

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